**Product data sheet** 

### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- MLPAK33 package (3.3 x 3.3 mm footprint)

## 3. Applications

- · High-side load switch
- Battery management
- DC-to-DC conversion
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-13.7	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -8.1 A; $T_j$ = 25 °C		-	14.4	18	mΩ
	resistance	$V_{GS}$ = -2.5 V; $I_D$ = -6.3 A; $T_j$ = 25 °C		-	22.5	30	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	D I
2	S	source		
3	S	source		G (F)
4	G	gate	l h d	s
5	D	drain		017aaa257
6	D	drain		
7	D	drain	MLPAK33 (SOT8002-1)	
8	D	drain		

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package							
	Name	Description	Version					
PXP018-20QX		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1					

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PXP018-20QX	8АН

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## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-13.7	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-8.4	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-5.1	Α
		V <sub>GS</sub> = -4.5 V; T <sub>sp</sub> = 25 °C		-	-39.7	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-55.4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	4.8	W
		T <sub>amb</sub> = 25 °C	[1]	-	1.8	W
		T <sub>sp</sub> = 25 °C		-	50	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode		'			
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.7	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

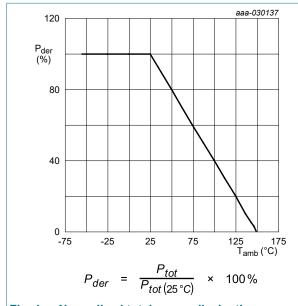


Fig. 1. Normalized total power dissipation as a function of ambient temperature

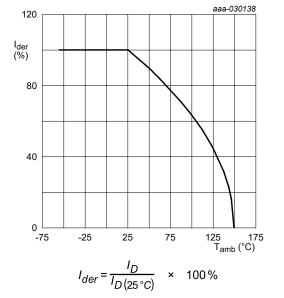


Fig. 2. Normalized continous drain current as a function of ambient temperature

#### 20 V, P-channel Trench MOSFET

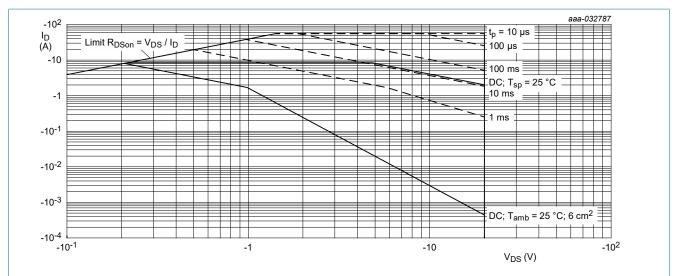


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

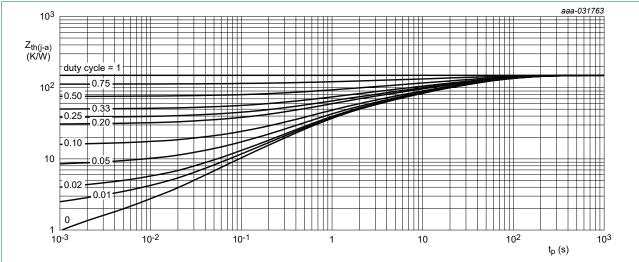
20 V, P-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

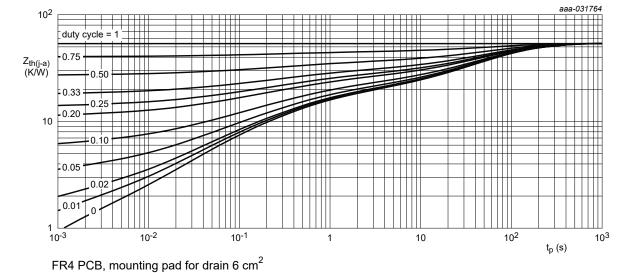
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance from		[1]	-	150	190	K/W
	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	21	26	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	2.1	3.1	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.7	-0.9	-1.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -8.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	14.4	18	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -8.1 A; $T_j$ = 150 °C	-	20.4	25.6	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -6.3 A; $T_j$ = 25 °C	-	22.5	30	mΩ
9fs	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -8.1 \text{ A}; T_j = 25 \text{ °C}$	-	23.2	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	4.6	-	Ω
Dynamic ch	aracteristics		1		<u> </u>	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -8.1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	23.2	34.8	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	4.1	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	2.1	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	2	-	nC
$Q_{GD}$	gate-drain charge		-	7.1	-	nC
$V_{GSpl}$	gate-source plateau voltage	$V_{DS}$ = -10 V; $I_{D}$ = -8.1 A; $T_{j}$ = 25 °C	-	-1.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2360	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	310	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	280	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -10 \text{ V}; I_D = -6.3 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	22	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	50	-	ns
t <sub>f</sub>	fall time	1	-	30	-	ns
Source-drai	in diode		1		-	
V <sub>SD</sub>	source-drain voltage	$I_S = -1.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = -1.7 \text{ A}$ ; $dI_S/dt = 100 \text{ A/µs}$ ;	-	23	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -4.5 \text{ V}; V_{DS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	10	-	nC
t <sub>a</sub>	reverse recovery rise time	1	-	9	-	ns
t <sub>b</sub>	reverse recovery fall time	-	-	14	-	ns

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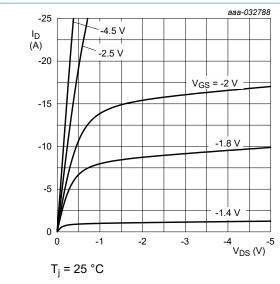


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

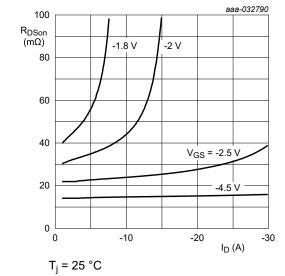


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

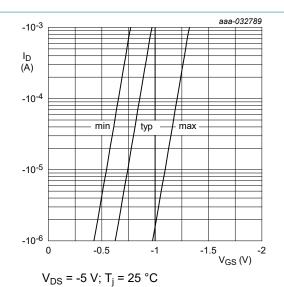


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

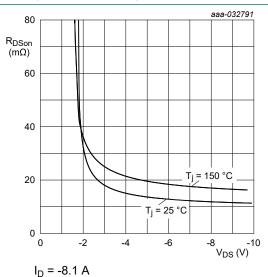


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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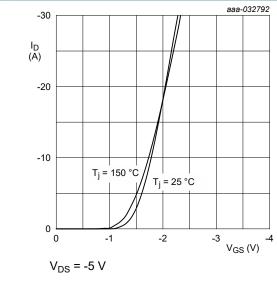


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

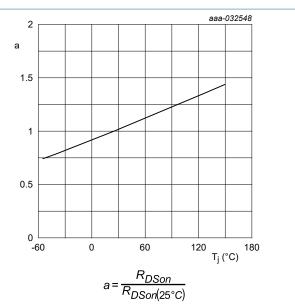


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

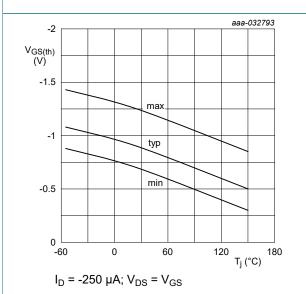


Fig. 12. Gate-source threshold voltage as a function of junction temperature

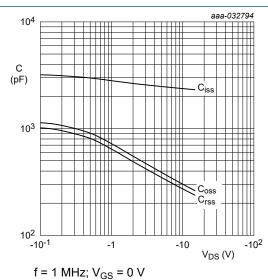


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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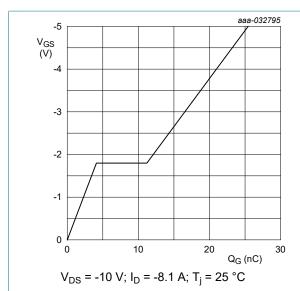


Fig. 14. Gate-source voltage as a function of gate charge; typical values

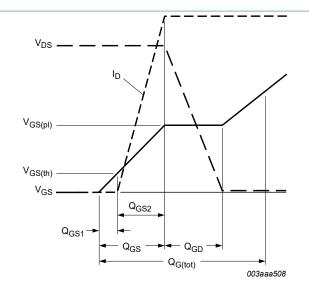


Fig. 15. Gate charge waveform definitions

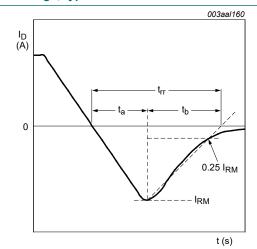


Fig. 16. Reverse recovery timing definition

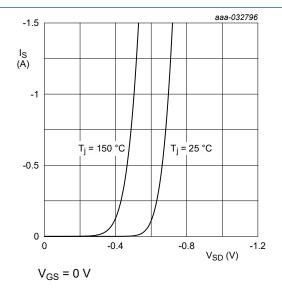
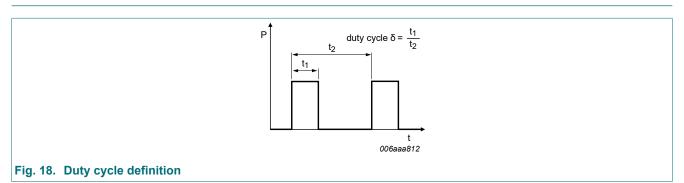


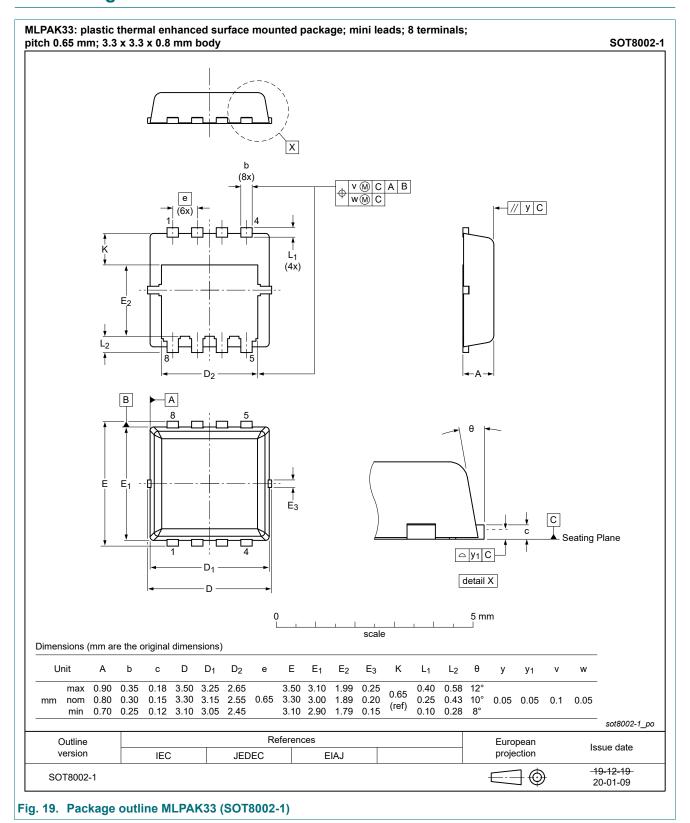
Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information



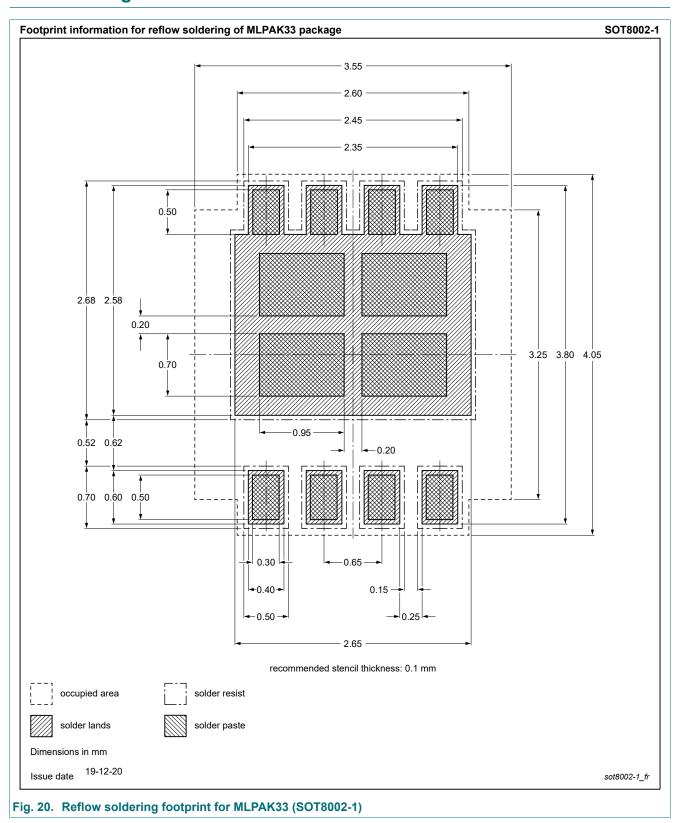
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## 12. Package outline



20 V, P-channel Trench MOSFET

## 13. Soldering



20 V, P-channel Trench MOSFET

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXP018-20QX v.1	20210105	Product data sheet	-	-

#### 20 V, P-channel Trench MOSFET

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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